			•	Application No.	Applicant(s)		Pag	e 1 of 1	
PT	O-144	9		Аррисацов но.					
	16.	4! Dinalaa	0!404ion	10/678,837	i i	Tomblad et al.			
	at the	rmation Disclos		Docket Number	Group Art U	Jnit Filing Da	te		
in an Application				068736.0231	2811	2811 Octobe		er 3, 2003	
YAM	0 9 20	15 5		U.S. PATENT DOCUMENT	S		1		
^		OCUMENT NO.	DATE	NAME	CLASS 257	SUBCLASS	FILING DATE		
No.	TANK	5132753	7/21/92	Chang et al.	337	23.4	3/2	3/90	
M	₽в	6613622	9/2/03	Nair et al.	438	188	7/1	5/02	
	C:				_				
	D.								
	E.					 -	<u> </u>		
	F.						<u> </u>		
	G.						<u> </u>		
	н.						<u> </u>		
	1		ļ		+		<u> </u>		
	J.								
	к.						ļ <u>.</u>		
	L.						ļ		
	М.				_		\		
	N.		·				+		
	О.		<u> </u>					/ -	
		FOREIGN PATENT DOCUMENTS						LATION	
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO	
	P.								
	Q.						-		
	R.		<u> </u>				1-1		
	S.						+-+		
	Т.						\Rightarrow		
	U.		<u> </u> _				<u> </u>		
		NON-PATEN	T DOCUMENTS - DO	CUMENT (Including Author	r, Title, Source, and Pe	ertinent Pages)			
11/1	v.	Dragon et al., "A Silicon MOS Process for Integrated RF Power Amplifiers," IEEE MTT-S Digest, Pages 257-260					6/1	7/96	
	W.						 		
	X.							<u></u>	
	Y.						-		
	Z.		1					$\overline{}$	
EY/	AMINE		7 /	$\overline{}$	DATE CONSIDER	ED , / ,	:1/	~	

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

U.S. Patent and Trademark Office